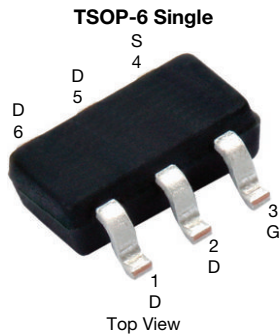


## P-Channel 80 V (D-S) MOSFET



Marking Code: BU

PRODUCT SUMMARY	
$V_{DS}$ (V)	-80
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = -10$ V	0.0827
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = -4.5$ V	0.1242
$Q_g$ typ. (nC)	5.6
$I_D$ (A) <sup>a</sup>	-5.4
Configuration	Single

ORDERING INFORMATION	
Package	TSOP-6 Single
Lead (Pb)-free and halogen-free	Si3129DV-T1-GE3

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DS}$	-80	V
Gate-source voltage	$V_{GS}$	$\pm 20$	
Continuous drain current ( $T_J = 150$ °C)	$I_D$	$T_C = 25$ °C	-5.4
		$T_C = 70$ °C	-4.4
		$T_A = 25$ °C	-3.8 <sup>b, c</sup>
		$T_A = 70$ °C	-3.0 <sup>b, c</sup>
Pulsed drain current ( $t = 300$ $\mu$ s)	$I_{DM}$	-20	A
Continuous source-drain diode current	$I_S$	$T_C = 25$ °C	
		$T_A = 25$ °C	-1.7 <sup>b, c</sup>
Single pulse avalanche energy	$I_{AS}$ $E_{AS}$		15
			11
Maximum power dissipation	$P_D$	$T_C = 25$ °C	4.2
		$T_C = 70$ °C	2.7
		$T_A = 25$ °C	2 <sup>b, c</sup>
		$T_A = 70$ °C	1.3 <sup>b, c</sup>
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to 150	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum Junction-to-Ambient <sup>b, d</sup>	$t \leq 5$ s	$R_{thJA}$	45	62.5	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	25	30	

**Notes**

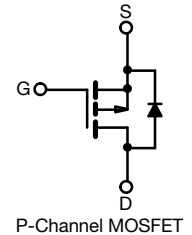
- $T_C = 25$  °C
- Surface mounted on 1" x 1" FR4 board
- $t = 5$  s
- Maximum under steady state conditions is 110 °C/W

**FEATURES**

- TrenchFET® power MOSFET
- 100 %  $R_g$  tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
 COMPLIANT  
 HALOGEN  
**FREE**
**APPLICATIONS**

- Power management for portable and consumer
  - Load switches
  - DC/DC converters



P-Channel MOSFET



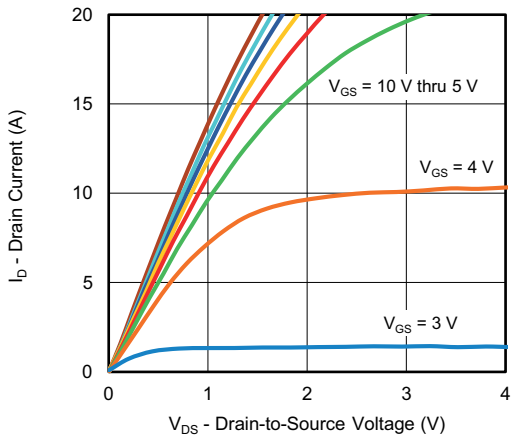
SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA	-80	-	-	V
V <sub>DS</sub> temperature coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = -10 mA	-	-115	-	mV/°C
V <sub>GS(th)</sub> temperature coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μA	-	4.8	-	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-1.5	-	-2.5	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = -80 V, V <sub>GS</sub> = 0 V	-	-	-10	μA
		V <sub>DS</sub> = -80 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C	-	-	-50	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≤ -5 V, V <sub>GS</sub> = -10 V	-5	-	-	A
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -3.8 A	-	0.0689	0.0827	Ω
		V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -3.1 A	-	0.0994	0.1242	
<b>Dynamic <sup>b</sup></b>						
Input capacitance	C <sub>iSS</sub>	V <sub>DS</sub> = -40 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	805	-	pF
Output capacitance	C <sub>oss</sub>		-	265	-	
Reverse transfer capacitance	C <sub>rSS</sub>		-	10	-	
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> = -40 V, V <sub>GS</sub> = -10 V, I <sub>D</sub> = -3.8 A	-	12	18	nC
		V <sub>DS</sub> = -40 V, V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -3.8 A	-	5.6	8.4	
Gate-source charge	Q <sub>gs</sub>	V <sub>DS</sub> = -40 V, V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -3.8 A	-	3.1	-	
Gate-drain charge	Q <sub>gd</sub>	V <sub>DS</sub> = -40 V, V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -3.8 A	-	1.4	-	
Gate resistance	R <sub>g</sub>	f = 1 MHz	0.8	4.4	8.8	Ω
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = -40 V, R <sub>L</sub> = 13.3 Ω I <sub>D</sub> ≅ -3 A, V <sub>GEN</sub> = -10 V, R <sub>g</sub> = 1 Ω	-	15	30	ns
Rise time	t <sub>r</sub>		-	8	16	
Turn-off delay time	t <sub>d(off)</sub>		-	25	50	
Fall time	t <sub>f</sub>		-	12	24	
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = -40 V, R <sub>L</sub> = 13.3 Ω I <sub>D</sub> ≅ -3 A, V <sub>GEN</sub> = -4.5 V, R <sub>g</sub> = 1 Ω	-	28	56	
Rise time	t <sub>r</sub>		-	42	84	
Turn-off delay time	t <sub>d(off)</sub>		-	24	48	
Fall time	t <sub>f</sub>		-	15	30	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous source-drain diode current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	-3.5	A
Pulse diode forward current	I <sub>SM</sub>		-	-	-20	
Body diode voltage	V <sub>SD</sub>	I <sub>S</sub> = -3 A, V <sub>GS</sub> = 0 V	-	-0.8	-1.2	V
Body diode reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = -3 A, dI/dt = 100 A/μs, T <sub>J</sub> = 25 °C	-	38	57	ns
Body diode reverse recovery charge	Q <sub>rr</sub>		-	50	75	nC
Reverse recovery fall time	t <sub>a</sub>		-	26	-	ns
Reverse recovery rise time	t <sub>b</sub>		-	12	-	

**Notes**

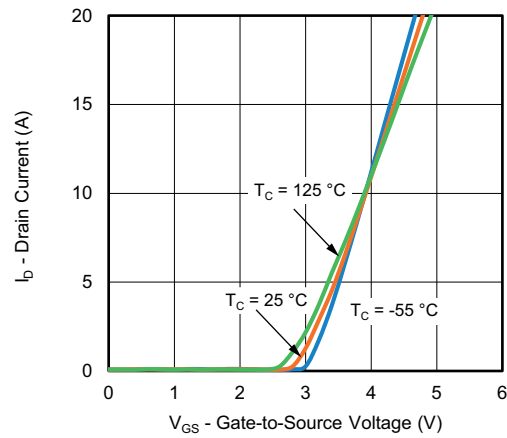
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

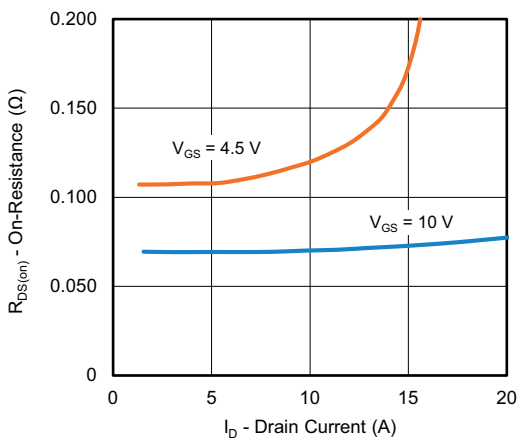
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



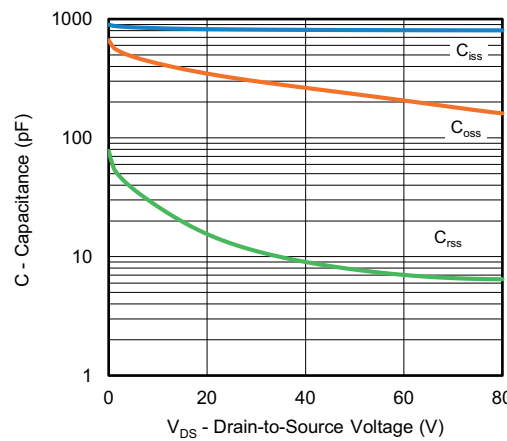
**Output Characteristics**



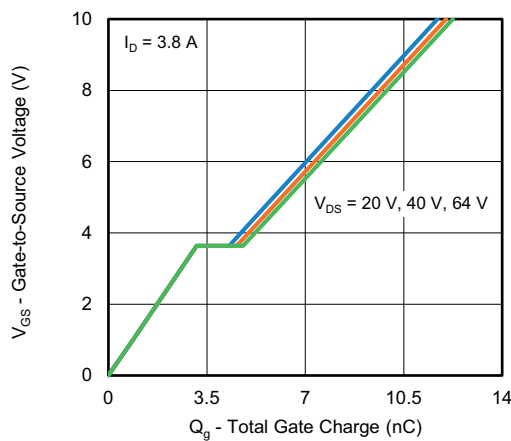
**Transfer Characteristics**



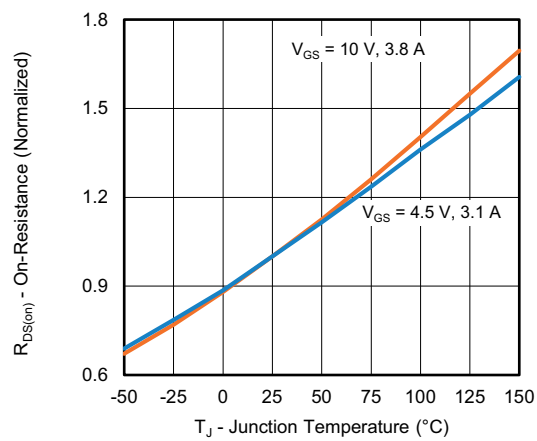
**On-Resistance vs. Drain Current**



**Capacitance**



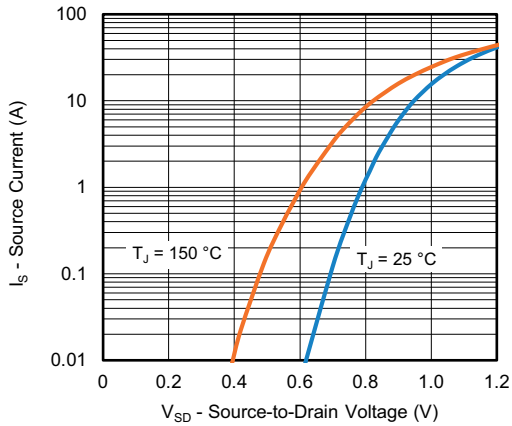
**Gate Charge**



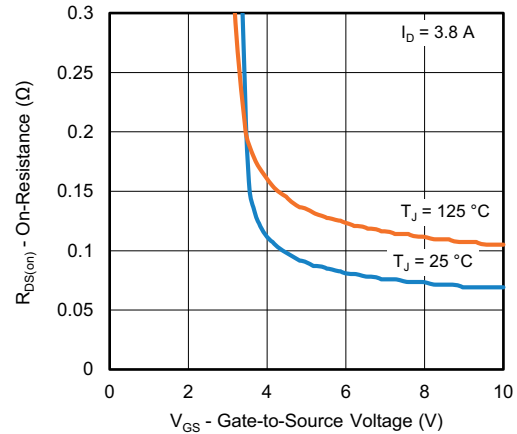
**On-Resistance vs. Junction Temperature**



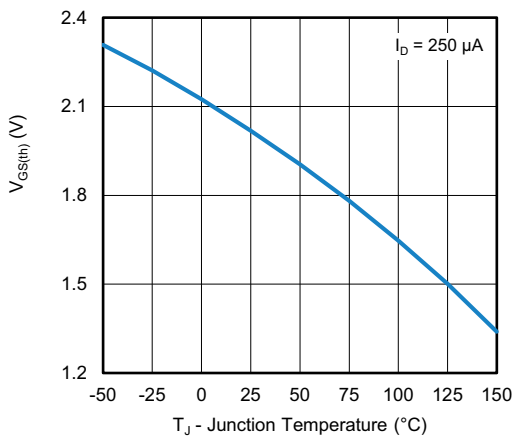
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



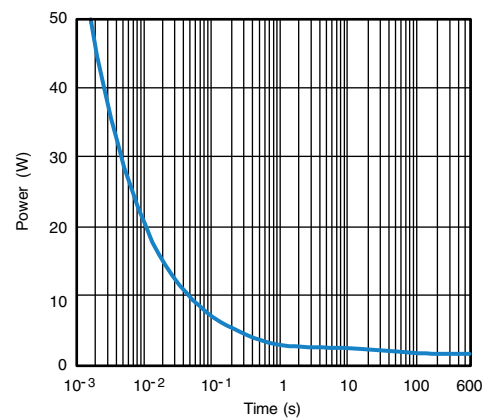
Source-Drain Diode Forward Voltage



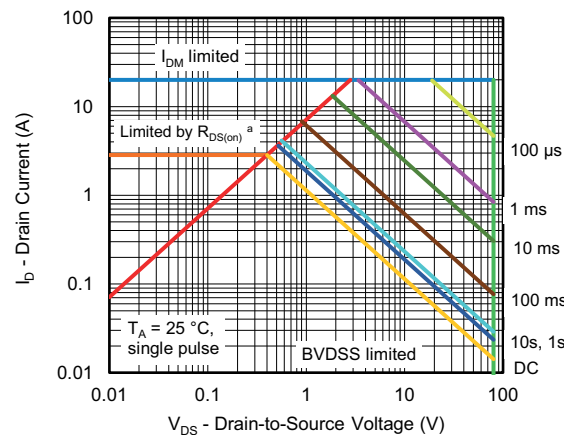
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient



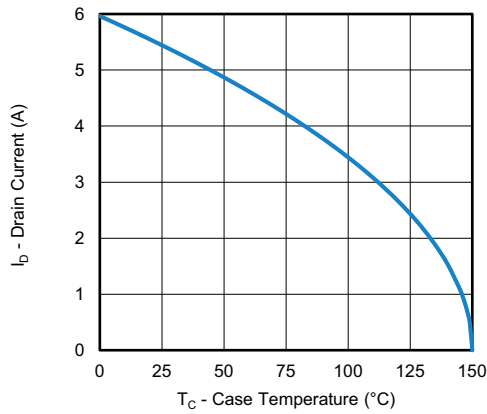
Safe Operating Area

Note

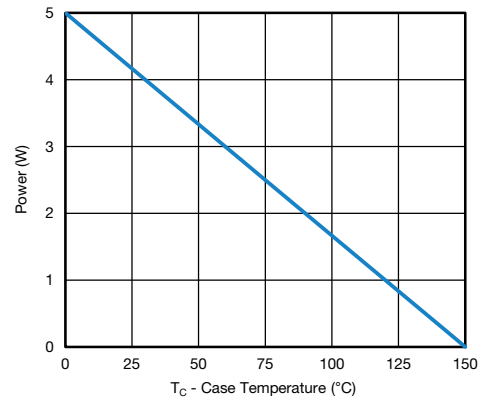
a.  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified



**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Current Derating <sup>a</sup>**



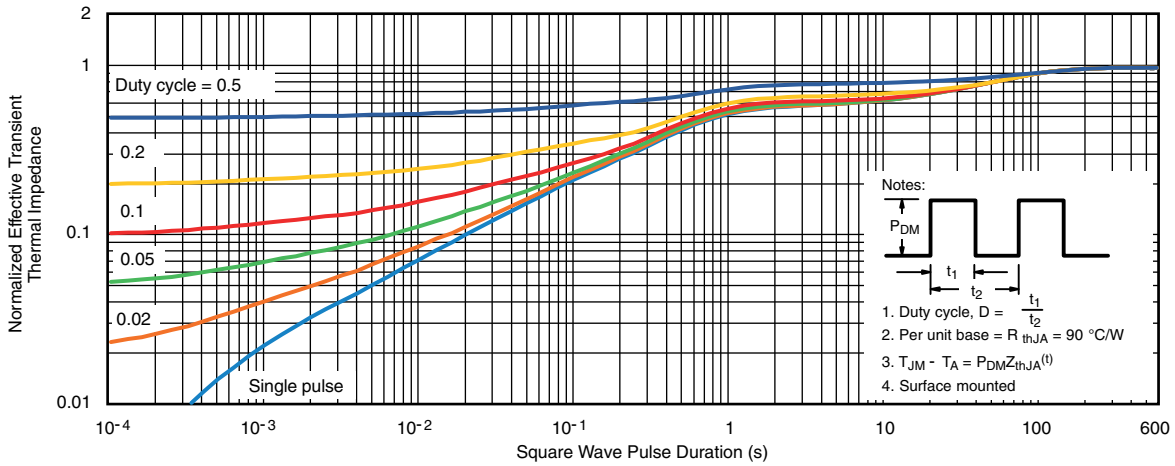
**Power Junction-to-Case**

**Note**

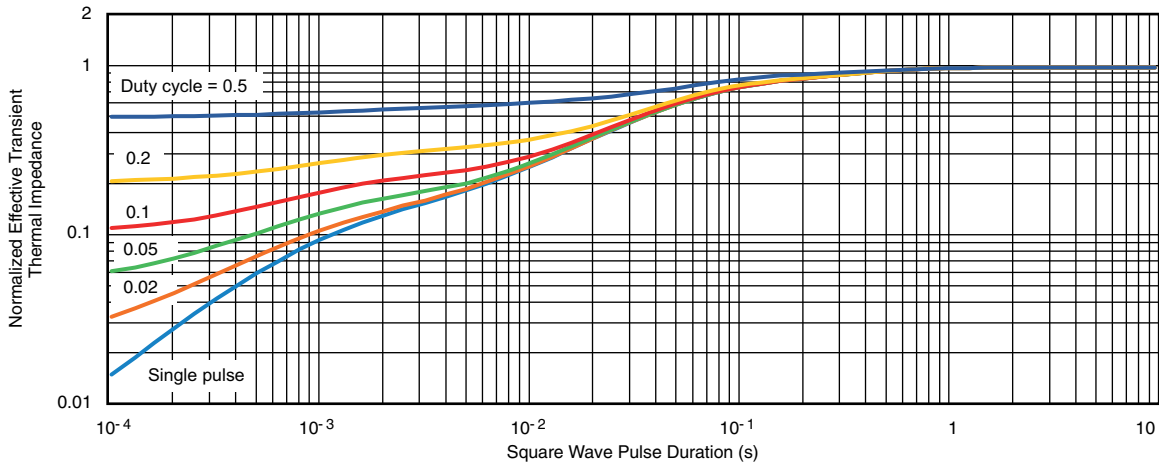
- a. The power dissipation P<sub>D</sub> is based on T<sub>J</sub> max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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